

isc Silicon NPN Power Transistor

2SC3320

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- High Reliability

APPLICATIONS

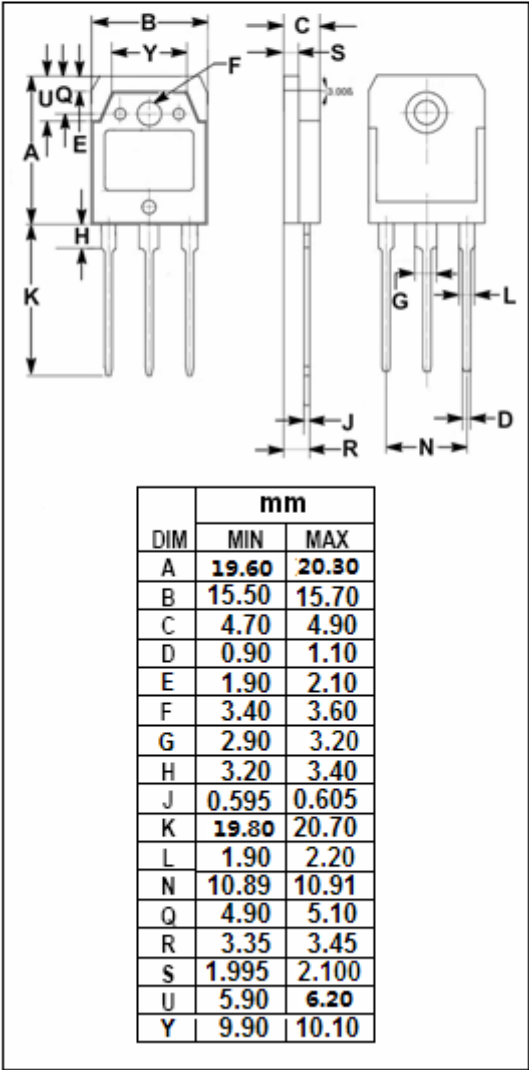
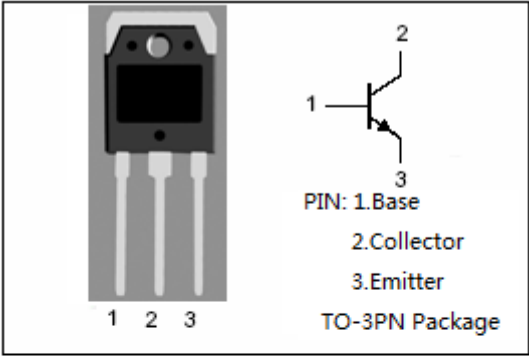
- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	80	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^{\circ}\text{C/W}$



isc Silicon NPN Power Transistor**2SC3320****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	400			V
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA ; I _B = 0	400			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA ; I _E = 0	500			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA ; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A ; I _B = 1.2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 500V ; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V ; I _C = 0			1.0	mA
h _{FE}	DC Current Gain	I _C = 6A ; V _{CE} = 5V	10			

Switching times

t _{on}	Turn-on Time	I _C = 7.5A , I _{B1} = 1.5A; I _{B2} = -3A R _L = 20Ω ; P _W =20μ s Duty≤2%			0.5	μ s
t _{stg}	Storage Time				1.5	μ s
t _f	Fall Time				0.15	μ s